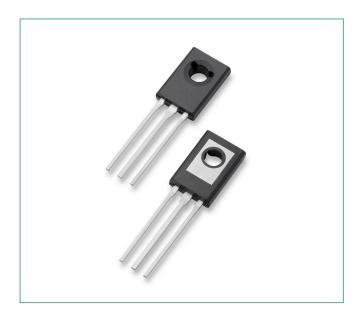


Surface Mount - 400V - 600V > MCR106-6, MCR106-8

MCR106-6, MCR106-8





Description

PNPN devices designed for high volume consumer applications such as temperature, light and speed control; process and remote control, and warning systems where reliability of operation is important.

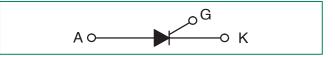
Features

- Glass-Passivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Pb-Free Packages are Available

Pin Out



Functional Diagram



Additional Information







Samples



Surface Mount - 400V - 600V > MCR106-6, MCR106-8

Maximum Ratings $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (– 40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR72-3 MCR72-6	V _{drm} , V _{rrm}	400 600	V
On-State RMS Current (180° Conduction Angles; $T_c = 93$ °C)	TM (RMS)	4.0	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, $T_J = 110^{\circ}$ C	I _{TSM}	25	А
Average On-State Current (180° Conduction Angles; $T_c = 93$ °C)	I _{T(AV)}	2.55	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	2.6	A ² s
Forward Peak Gate Power (($T_c = 93^{\circ}C$, Pulse Width $\leq 1.0 \mu s$)	V _{GM}	0.5	W
Forward Average Gate Power, (T _C = 93°C, t = 8.3 ms)	I _{GM}	0.1	А
Forward Peak Gate Current, (T _C = 93°C, Pulse Width ≤ 1.0 µs)	I _{GM}	0.2	W
Peak Reverse Gate Voltage, (T _C = 93°C, Pulse Width ≤ 1.0 μs)	V _{RGM}	6.0	W
Operating Junction Temperature Range	T _J	-40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Mounting Torque	_	6.0	in. lb.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{sJC}	3.0	°C/W
Thermal Resistance, Junction-to-Ambient	R _{sJA}	75	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{2.} Torque rating applies with use of compression washer (B52200-F006 or equivalent). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common. (See AN209B). For soldering purposes (either terminal connection or device mounting), soldering temperatures shall not exceed +200°C. For optimum results, an activated flux (oxide removing) is recommended.

Thyristors

Electrical Characteristics - **OFF** (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Forward or Reverse Blocking Current ($V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, R_{GK} = 1 \text{ k}\Omega$)	$T_{_{\rm J}} = 25^{\circ}\text{C}$	l _{DRM} ,	-	-	10	
	T _J = 110°C	I _{RRM}	-	-	200	μΑ

Electrical Characteristics - **ON** $(T_J = 25^{\circ}\text{C unless otherwise noted})$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 3) (I _{TM} = 4 A Peak)		V _{TM}	-	-	2.0	V
Gate Trigger Current (Continuous dc) (Note 4)	$(V_{AK} = 7 \text{ Vdc};$ $R_{L} = 100 \Omega)$		-	-	200	μΑ
date ingger current (continuous de) (Note 4)	$(T_{c} = -40^{\circ}C)$	I _{GT}	-	-	500	
Gate Trigger Voltage (Continuous dc) (Note 4) ($V_D = 12 \text{ V}; R_L = 100 \Omega$)			-	_	1.0	V
Gate Trigger Non-Trigger Voltage (Note 4) $V_{AK} = 7 \text{ Vdc}; R_{L} = 100 \Omega$)		V _{GD}	0.2	-	_	V
Holding Current ($V_D = 12 \text{ V}$, Initiating Current = 200 mA, $R_{GK} = 1 \text{k}\Omega$)		I _H	_	_	5.0	mA

Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off–State Voltage $(R_{GK} = 1 \text{ k } \Omega, T_J = 110^{\circ}\text{C})$	dv/dt	-	10	-	V/µs

^{3.} Pulse Test: Pulse Width \leq 1.0 ms, Duty Cycle \leq 1%.

^{4.} R_{GK} current is not included in measurement.



Voltage Current Characteristic of SCR

Symbol	Parameter	
V_{DRM}	Peak Repetitive Forward Off State Voltage	
I _{DRM}	Peak Forward Blocking Current	
V _{RRM}	Peak Repetitive Reverse Off State Voltage	
I _{RRM}	Peak Reverse Blocking Current	
V _{TM}	Maximum On State Voltage	
I _H	Holding Current	

Thyristors

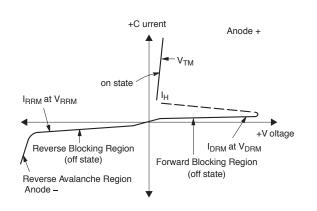


Figure 1. Average Current Derating

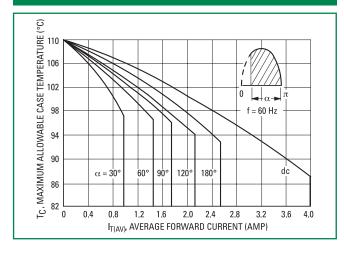
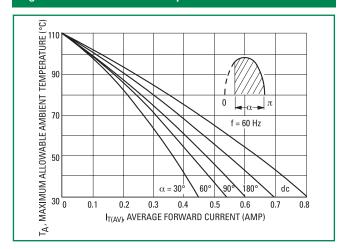
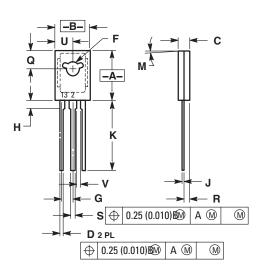


Figure 2. On-State Power Dissipation



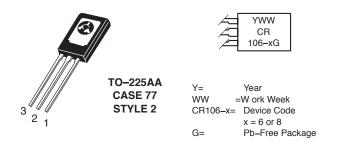
Dimensions



<u> </u>	Incl	Inches Millin		neters	
Dim	Min	Max	Min	Max	
А	0.425	0.435	10.80	11.04	
В	0.295	0.305	7.50	7.74	
С	0.095	0.105	2.42	2.66	
D	0.020	0.026	0.51	0.66	
F	0.115	0.130	2.93	3.30	
G	0.094	BSC	2.39 BSC		
Н	0.050	0.095	1.27	2.41	
J	0.015	0.025	0.39	0.63	
K	0.575	0.655	14.61	16.63	
М	5 T	5 TYP		ΥP	
Q	0.148	0.158	3.76	4.01	
R	0.045	0.065	1.15	1.65	
S	0.025	0.035	0.64	0.88	
U	0.145	0.155	3.69	3.93	
V	0.040		1.02		

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
- 3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

Part Marking System



Pin Assignment				
1	Cathode			
2	Anode			
3	Gate			

Ordering Information					
Package	Shipping				
TO-225AA					
TO-225AA (Pb-Free)	500 Units / Box				
TO-225AA					
TO-225AA (Pb-Free)					
	Package TO-225AA TO-225AA (Pb-Free) TO-225AA TO-225AA				

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